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DERWENT- 200214

WEEK:

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TITLE: Method for processing chamber seasoning for increasing average cleaning frequency of a chamber in semiconductor device fabrication process -
NoAbstract

INVENTOR: WOO, B J

PRIORITY-DATA: 1998KR-0063175 (December 31, 1998)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
KR <u>2000046489</u>	A July 25, 2000	N/A	000	H01L 021/02
KR 279907 B	March 2, 2001	N/A	000	H01L 021/02

INT-CL (IPC): H01L021/02

ABSTRACTED-PUB-NO: KR2000046489A

EQUIVALENT-ABSTRACTS:

STN Columbus

metallic layer which is formed over an insulator film on a semiconductor substrate to provide a patterned circuit/resist layer with etching-residual protective sidewalls, (2) removing the protective sidewalls by rotary-leaf washing with a **fluoro** compd. agent, (3) **cleansing** with purified water, and (4) drying the semiconductor devices by rotating the substrates. The process gives the semiconductor devices complete removal of the sidewall residues and protection against corrosion.

L17 ANSWER 18 OF 26 CAPLUS COPYRIGHT 2007 ACS on STN

Full Text

AN 2002:206812 CAPLUS

DN 136:225327

TI Chamber seasoning method for increasing mean **cleaning** cycle of chamber

IN Woo, Bong Ju

PA Korea Ram Research Co., Ltd., S. Korea

SO Repub. Korean Kongkae Taeho Kongbo, No pp. given

CODEN: KRXXA7

DT Patent

LA Korean

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	KR 2000046489	A	20000725	KR 1998-63175	19981231
PRAI	KR 1998-63175		19981231		

AB An improved chamber seasoning method is provided to increase a mean **cleaning** cycle of a chamber in a process for forming a tungsten plug. Before or During the process for forming a tungsten plug, a chamber is seasoned after a dry **clean** operation and before a wafer is introduced into the chamber. In particular, for the seasoning method, chlorine gas or **chloride** gas such as **boron chloride** is employed with an etch gas or alone to remove contaminations such as **aluminum oxide** that occur naturally within chamber components. The etch gas may include sulfur **fluoride**, argon, or nitrogen. Furthermore, the chlorine or chloride gas removes contaminations such as **aluminum fluoride** that occur by the use of the **fluoride** gas as the etch gas. In a conventional seasoning method, contaminations are increased when approx. seven hundred twenty five wafers were treated. On the other hand, the improved seasoning method controls the occurrence of contaminations until approx. one thousand two hundred seventy five wafers are treated.

L17 ANSWER 19 OF 26 CAPLUS COPYRIGHT 2007 ACS on STN

Full Text

AN 2001:91477 CAPLUS

DN 134:140429

TI Method of manufacturing a gate electrode in a semiconductor device

IN Seo, Hwan Seok; Lee, Sang Hyeob

PA Hyundai Electronics Industries Co., Ltd., S. Korea

SO U.S., 8 pp.

CODEN: USXXAM

DT Patent

LA English

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 6184113	B1	20010206	US 1999-342530	19990629
	KR 2000003477	A	20000115	KR 1998-24719	19980629
PRAI	KR 1998-24719	A	19980629		

AB The present invention relates to a method for manufg. a semiconductor device having a gate electrode (e.g. W gate electrode) of low resistivity.

